#### **LISTING OF THE CLAIMS:**

Claim 1 (Withdrawn) A method of forming a plurality of conductive structures on a substrate comprising the steps of:

forming a first semiconductor structure of a first conductivity type, a second semiconductor structure of a second conductivity type, and a third semiconductor structure on a substrate, said third semiconductor structure is disposed between said first and second semiconductor structures and is separated therefrom by an insulator structure;

depositing an interconnect layer over at least said first, second and third semiconductor structures;

forming a planarizing conductor on said interconnect layer, said
planarizing conductor having etch characteristics similar to those of said interconnect
layer and said first and second semiconductor structures, but different from those of said
insulator structure; and

patterning and etching said planarizing conductor, said interconnect layer, and said first and second semiconductor structures so that each has at least one lateral dimension that is substantially the same.

Claim 2 (Withdrawn) The method of Claim 1 wherein said first and second semiconductor structures are formed utilizing a double angled implant such that vertical surfaces of a polySi-containing or semiconducting layer formed abutting said insulator structure are oppositely doped, while horizontal surfaces of said polySi-containing or semiconducting layer are doubly doped.

Claim 3 (Withdrawn) The method of Claim 2 wherein said polySicontaining layer is comprised of polySi.

Claim 4 (Withdrawn) The method of Claim 2 wherein said polySicontaining layer is comprised of polySiGe.

Claim 5 (Withdrawn) The method of Claim 2 wherein said double angled implant is performed so as to provide implant regions whose final dopant concentration is on the order of from about 1E19 to about 1E21 atoms/cm<sup>3</sup>.

Claim 6 (Withdrawn) The method of Claim 1 wherein said insulator structure includes a gate dielectric and a hard mask.

Claim 7 (Withdrawn) The method of Claim 1 wherein said interconnect layer is a metallic layer which is capable of preventing dopant diffusion into said first and second semiconductor structures.

Claim 8 (Withdrawn) The method of Claim 1 wherein said planarizing conductor is comprised of a polySi-containing material, a conductive metal, a conductive metal alloy or a semiconducting material.

Claim 9 (Withdrawn) The method of Claim 8 wherein said planarizing conductor is comprised of polySi or polySiGe.

Claim 10 (Withdrawn) The method of Claim 1 further comprising annealing said interconnect layer so as to convert said layer into a metal silicide or metal nitride.

Claim 11 (Withdrawn) The method of Claim 10 wherein said annealing is carried out at a temperature of about 700°C or higher and in the presence of an inert gas atmosphere.

Claim 12 (Currently Amended) An asymmetric field effect transistor (FET) comprising:

a patterned stack including at least a vertical semiconductor body having sidewalls located on an upper non-recessed surface of an insulator that is located on a substrate;

a gate dielectric located on each sidewall of said vertical semiconductor body;

a p-type gate portion located on one side of the vertical semiconductor body and an n-type gate portion located on an opposing side of the vertical semiconductor body, said gate portions together with said vertical semiconductor body forming an a single asymmetric FET device that is located on said upper surface of the insulator and are separated from the vertical semiconductor body by said gate dielectric;

a double implanted region located adjacent to each of said gate portions and on said insulator;

an interconnect located at least over said p-type gate portion and said n-type gate portion; and

a planarizing structure above said interconnect.

### 13. (Cancelled)

- 14. (Original) The asymmetric FET of Claim 12 wherein said p-type gate portion, said n-type gate portion and said planarizing structure are composed of a polySicontaining material or a semiconducting material.
- 15. (Original) The asymmetric FET structure of Claim 14 wherein said polySi-containing material comprises polySi or polySiGe.
- 16. (Original) The asymmetric FET of Claim 12 wherein said interconnect is highly resistant to dopant diffusion.
- 17. (Original) The asymmetric FET of Claim 12 wherein said interconnect is a conductive metal, metal silicide or metal nitride.
- 18. (Original) The asymmetric FET of Claim 12 wherein said planarizing structure is doped polysilicon.
  - 19. (Cancelled)

- 20. (Original) The asymmetric FET of Claim 12 wherein said vertical semiconductor body has a hard mask present on an upper surface.
- 21. (Previously Presented) The asymmetric FET of Claim 20 wherein said hard mask is comprised of an oxide, nitride, oxynitride or multilayers thereof.
- 22. (Original) The asymmetric FET of Claim 12 wherein said n-type gate portion is comprised of N-doped polysilicon and said p-type gate portion is comprised of P-type polysilicon.
  - 23. (Cancelled)
- 24. (Previously Presented) The asymmetric FET of Claim 12 wherein said vertical semiconductor body and said substrate are components of a silicon-on-insulator material.
- 25. (Original) The asymmetric FET of Claim 12 wherein said planarizing material is a metal or metal alloy.
- 26. (Original) The asymmetric FET of Claim 12 further comprising source/drain regions in areas adjacent to the vertical semiconductor body.

- 27. (Original) The asymmetric FET of Claim 26 wherein said source/drain regions are doped so as to have either donor or acceptor impurities.
- 28. (Currently Amended) An asymmetric field effect transistor (FET) comprising:
- a patterned stack including at least a vertical single crystal Si semiconductor body having sidewalls located on an upper non-recessed surface of an insulator that is located on a substrate;
- a gate dielectric located on each sidewall of said vertical single crystal Si semiconductor body;
- a p-type gate portion located on one side of the vertical single crystal Si semiconductor body and an n-type gate portion located on an opposing side of the vertical single crystal Si semiconductor body, said p-type and n-type gate portions are composed of polysilicon, and said gate portions together with said vertical single crystal Si semiconductor body forming an a single asymmetric FET device that is located on said upper surface of the insulator and are separated from the vertical single crystal Si semiconductor body by said gate dielectric;
- a double implanted region located adjacent to each of said gate portions and on said insulator;
- a metal silicide interconnect located at least over said p-type gate portion and said n-type gate portion; and
  - a planarizing doped polysilicon layer above said interconnect.

Respectfully submitted,

Kevin T. Wakley (OB #32569) SPROUSE SHRADER SMITH PLLC 110 W. 7<sup>th</sup> St., Ste 2710 Tulsa, OK 74119

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kevin.wakley@sprouselaw.com

Attorney for Plaintiff

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# Office of Attorney General State of Oklahoma

February 26, 2016

Tracy W. Robinett Robinett, Swartz & Aycock 624 S. Boston Avenue, Suite 900 Tulsa, Oklahoma 74119

Re: Whalen G. King v. Southwest Aviation Specialists OCRE Complaint No.: CR-15-0065-E

Dear Mr. Robinette:

The Office of Civil Rights Enforcement ("OCRE") has issued the enclosed Notice of Right to Sue (Conciliation Failure) finding that based on the consideration of the evidence acquired in the investigation there is reasonable cause that Respondent violated the Act and discriminated against the Complainant. Complainant has ninety (90) days from receipt of this Notice of Rights to file a lawsuit under state law in a district court of the State of Oklahoma.

Respectfully,

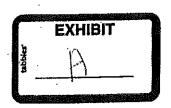
Kara I. Smith

Chief Assistant Attorney General

Office of Civil Rights Enforcement Unit, Chief

KIS/tc Enclosure

cc w/encl.: Whalen G. King, Complainant





# OKLAHOMA ATTORNEY GENERAL OFFICE OF CIVIL RIGHTS ENFORCEMENT

### NOTICE OF RIGHT TO SUE

(CONCILIATION FAILURE)

From:

Whalen G. King 6551 E. 31<sup>st</sup> St., #14 Tulsa, OK 74145

Office of Civil Rights Enforcement 15 W: 6th Street, Suite 1000 Tulsa, Oklahoma 74119

Complaint/Charge No.

OCRE Representative

Telephone No.

OCRE # CR-15-0065-E

Kara I. Smith

(918) 581-2885

EEOC#

Assistant Attorney General

#### TO THE COMPLAINANT:

This Notice concludes the OCRE's processing of the above-numbered Complaint or Charge at this time. The OCRE found reasonable cause that the respondent(s) engaged in a discriminatory practice but could not obtain a settlement with the respondent(s) through conciliation that would provide relief for you. The OCRE may file suit against the respondent(s) or it may close its file in this case. Closure does not mean the OCRE will not file suit against the respondent(s) later or intervene in your lawsuit if you decide to sue on your own behalf.

### -NOTICE OF SUIT RIGHTS-

Oklahoma Anti-Discrimination Act, Okla. Stat. tit. 25, § 1101 et seq., Title VII of the Civil Rights Act of 1964, the Americans with Disabilities Act, the Genetic Information Nondiscrimination Act, and/or the Age Discrimination in Employment Act: This will be the only notice of your right to sue that we will send you. You may file a lawsuit against the respondent(s) under state law in a district court of the State of Oklahoma. You also may have the right to file suit under federal law in federal or state court if federal law applies to the respondent(s). Your lawsuit MUST be filed WITHIN 90 DAYS from your receipt of this Notice or your right to sue based on this charge will be lost.

Equal Pay Act (EPA): EPA suits must be filed in federal or state court within two years (three years for willful violations) of the alleged EPA underpayment. This means that backpay due for any violations that occurred more than two years (three years) before you file suit may not be collectible.

If you file suit based on this Complaint or Charge, please send a copy of your file-stamped Petition or Complaint to this office.

On behalf of the OCRE

Kara I. Smith

Chief Assistant Attorney General Office of Civil Rights Enforcement Unit Chief (Date Mailed)

2.26.2016

Southwest Aviation Specialists, LLC c/o Tracy W. Robinett, Attorney for Respondent

CC:



# Office of Attorney General State of Oklahoma

Charging Party:

Whalen King

6551 E. 31st St. #14 Tulsa, Oklahoma 74145

Respondent:

Southwest Aviation Specialties, LLC

Attn: David Guzman 8720 Jack Bates Ave. Tulsa, Oklahoma 74132

RE:

Whalen King v. Southwest Aviation Specialties, LLC

OCRE Charge No.: CR-15-0065-E

# NOTICE OF DETERMINATION

Pursuant to the authority vested in me by the Attorney General of the State of Oklahoma and the Oklahoma Anti-Discrimination Act, Okla. Stat. Ann. tit. 25, § 1101 et seq. (the "Act"), I issue the following determination as to the merits of the above referenced charge: There is reasonable cause that Respondent discriminated against Charging Party on the basis of his race and retaliated against Charging Party for opposing unlawful activity in violation of the Act.

All requirements for coverage have been met. Charging Party timely filed the referenced complaint of employment discrimination with the Office of Civil Rights Enforcement ("OCRE") on April 13, 2015, asserting allegations sufficient to invoke the jurisdiction of the OCRE. Respondent is an employer within the meaning of the Act, and Charging Party was an employee of Respondent within the meaning of the Act.

Charging Party alleges Respondent discriminated against him on the basis of his race by subjecting him to racial harassment. Charging Party alleges that on or about March 9, 2015, he was subjected to objectionable treatment when his supervisor, Bill Copple, used the "N" word on two occasions. On or about March 12, 2015, in the presence of co-workers, Charging Party expressed his dissatisfaction about Mr. Copple's use of the "N" word and Charging Party's recent pay raise. Charging Party also stated that he was going to start looking for another job. Charging Party alleges on or about March 20, 2015, Respondent discharged him.

Respondent denies it discriminated against Charging Party. Respondent alleges to aware that Charging Party was upset about his pay raise and was going to start looking for another job, but was unaware Charging Party expressed opposition to the use of the "N" word. Respondent



OCRE Charge No.: CR-15-0065-E

Notice of Determination

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alleges it accepted Charging Party's resignation and did not discharge him. Charging Party alleges he did not resign or submit his two-weeks' notice. From the examination of the evidence, there is witness testimony that Respondent's management was aware Charging Party expressed opposition about the use of the "N" word, complained about his pay raise, and stated he was going to start looking for another job. The investigation revealed that Respondent was aware of the racial harassment and failed to take prompt and effective corrective action. Examination of the evidence establishes that Respondent discriminated against and subjected Charging Party to harassment on the basis of his race in violation of the Act. Having considered the evidence acquired in the investigation, I find there is reasonable cause that Respondent violated the Act.

In addition, Charging Party alleges he engaged in protected activity by opposing unlawful discrimination when he objected to Mr. Copple's discriminatory remark on or about March 12, 2015. Charging Party alleges on or about March 20, 2015, Respondent's management discharged him. Respondent alleges it accepted Charging Party's resignation early rather than allowing Charging Party the opportunity to serve his full two weeks. Charging Party alleges he did not resign or submit his two-weeks' notice. The investigation revealed that Respondent's management was made aware that Charging Party expressed his opposition to Mr. Copple's use of the "N" word prior to Respondent's management discharging Charging Party.

Examination of the evidence establishes there is reasonable cause that Respondent retaliated against Charging for engaging in protected activity by opposing unlawful discrimination. Having considered the evidence acquired in the investigation, I find there is reasonable cause that Charging Party's legally protected activity was a significant factor motivating the adverse action taken against Charging Party and that Respondent violated the Act by retaliating against the Charging Party.

### INVITATION TO CONCILIATE

Upon finding reasonable cause that Respondent violated the law, the OCRE seeks to eliminate the alleged unlawful employment practices by informal methods of conciliation pursuant to § 1502.6 of the Act. To this end, the OCRE now requests that the parties join with it in reaching a just resolution of this matter.

Pursuant to § 1502.6, nothing said or done in the course of conciliation may be made public or used as evidence in a subsequent proceeding without the written consent of the persons concerned. A conciliation agreement, if reached, shall be made public unless the Charging Party and Respondent agree otherwise, and the Attorney General determines that disclosure is not necessary to further the purpose of the Act.

Both the Charging Party and the Respondent must contact the OCRE within fifteen (15) days of receipt of this Notice to confirm whether they consent to attempt conciliation of the dispute.

OCRE Charge No.: CR-15-0065-E

Notice of Determination

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If Respondent declines to engage in conciliation or if a settlement acceptable to the Attorney General is not obtained, the Chief of the OCRE will inform the parties and further advise them of the court enforcement alternative available to the Charging Party and the OCRE.

<u>2.10.16</u> Date

Kara I Smith

Assistant Attorney General

Chief, Office of Civil Rights Enforcement

ce: David Guzman